

**A SEMICONDUCTOR DEVICE HAVING AN ANGLED  
COMPENSATION IMPLANT AND METHOD OF MANUFACTURE THEREFOR**

**ABSTRACT OF THE DISCLOSURE**

The present invention provides a semiconductor device 200 having an angled compensation implant, a method of manufacture therefore and a method of manufacturing an integrated circuit including the angled compensation implant. In one embodiment, the method of manufacturing the semiconductor device 200 includes creating a halo implant 240 in a substrate 210, introducing a compensation implant 260 in the substrate 210 at an angle abnormal to the substrate 210 and forming a source/drain region 250 above the compensation implant 260, the angle reducing a capacitance associated with the halo implant 240 or the source/drain region 250. The method further includes placing a gate structure 230 over the substrate 210.